

NVRAM NVSRAM Parallel 256Kbit 5V 28-Pin EDIP

Manufacturer: [Analog Devices, Inc](#)

Package/Case: DIP

Product Type: Memory

RoHS: RoHS Compliant/Lead free 

Lifecycle: Active



Images are for reference only

[Inquiry](#)

General Description

The DS1230 256k Nonvolatile (NV) SRAMs are 262,144-bit, fully static, nonvolatile SRAMs organized as 32,768 words by 8 bits. Each NV SRAM has a self-contained lithium energy source and control circuitry which constantly monitors VCC for an out-of-tolerance condition. When such a condition occurs, the lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent data corruption. DIP-package DS1230 devices can be used in place of existing 32k x 8 static RAMs directly conforming to the popular byte-wide 28-pin DIP standard. The DIP devices also match the pinout of 28256 EEPROMs, allowing direct substitution while enhancing performance. DS1230 devices in the Low Profile Module package are specifically designed for surface-mount applications. There is no limit on the number of write cycles that can be executed and no additional support circuitry is required for microprocessor interfacing.

Key Features

CC

CC

Recommended For You

DS1230Y-100+

Analog Devices, Inc

DIP

DS1225AB-150+

Analog Devices, Inc

DIP

DS1321S+T&R

Analog Devices, Inc

SOIC(N)

DS1220AB-100+

Analog Devices, Inc

DIP

DS28E15Q+U

Analog Devices, Inc

TDFN

DS1250ABP-100+

Analog Devices, Inc

SMDSMT

DS1330WP-150+

Analog Devices, Inc
SMDSMT

DS1245WP-150+

Analog Devices, Inc
PCM-34

DS1330YP-70+

Analog Devices, Inc
34-POWERCAPMODULE

DS2460S+T&R

Analog Devices, Inc
SOP8

DS1245AB-120+

Analog Devices, Inc
MOD32

DS1249Y-70

Analog Devices, Inc
DIP

DS1220AB-150IND+

Analog Devices, Inc
FBGA

DS1250AB-100

Analog Devices, Inc
DIP-32

DS1330WP-100IND+

Analog Devices, Inc
SMDSMT